

## N-Channel Enhancement Mode Power MOSFET

### Description

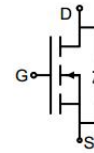
The GT55N06D5 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge. It can be used in a wide variety of applications.

### General Features

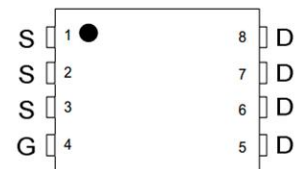
- $V_{DS}$  60V
- $I_D$  (at  $V_{GS} = 10V$ ) 45A
- $R_{DS(ON)}$  (at  $V_{GS} = 10V$ ) < 9m $\Omega$
- $R_{DS(ON)}$  (at  $V_{GS} = 4.5V$ ) < 13m $\Omega$
- 100% Avalanche Tested
- RoHS Compliant

### Application

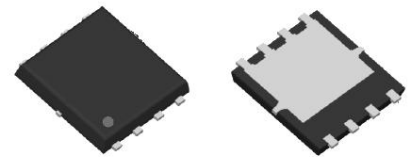
- Power switch
- DC/DC converters



Schematic diagram



pin assignment



DFN5\*6-8L

### Ordering Information

Device	Package	Marking	Packaging
GT55N06D5	DFN5*6-8L	GT55N06	5000pcs/Reel

### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ , unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	60	V
Continuous Drain Current	$I_D$	45	A
Pulsed Drain Current (note1)	$I_{DM}$	180	A
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Power Dissipation	$P_D$	69	W
Single pulse avalanche energy (note2)	$E_{AS}$	49	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 To 150	$^\circ\text{C}$

### Thermal Resistance

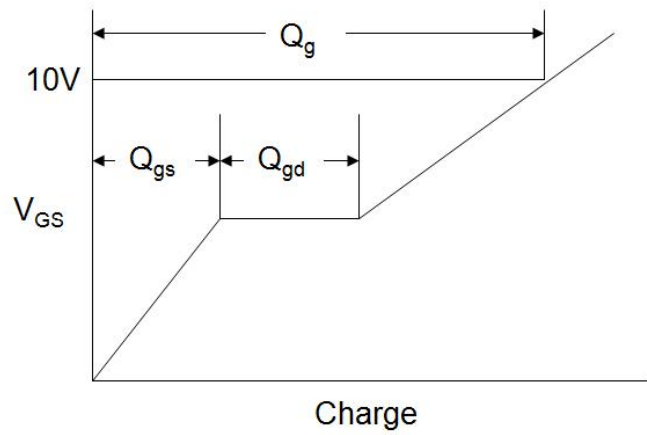
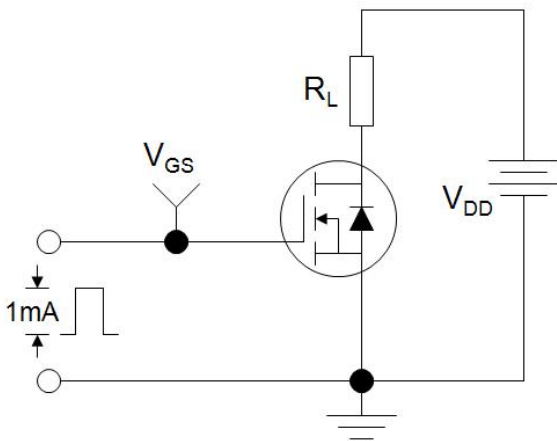
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient	$R_{thJA}$	17	$^\circ\text{C/W}$
Maximum Junction-to-Case	$R_{thJC}$	1.8	$^\circ\text{C/W}$

Specifications $T_J = 25^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
<b>Static Parameters</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	60	--	--	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 60V, V_{GS} = 0V$	--	--	1	$\mu A$
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 20V$	--	--	$\pm 100$	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1	1.4	2.4	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 14A$	--	7	9	m $\Omega$
		$V_{GS} = 4.5V, I_D = 10A$	--	10	13	
Forward Transconductance	$g_{FS}$	$V_{DS} = 5V, I_D = 14A$	--	30	--	S
<b>Dynamic Parameters</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0V,$ $V_{DS} = 30V,$ $f = 1.0MHz$	--	1085	--	pF
Output Capacitance	$C_{oss}$		--	316	--	
Reverse Transfer Capacitance	$C_{rss}$		--	22	--	
Total Gate Charge	$Q_g$	$V_{DD} = 30V,$ $I_D = 20A,$ $V_{GS} = 10V$	--	31	--	nC
Gate-Source Charge	$Q_{gs}$		--	6	--	
Gate-Drain Charge	$Q_{gd}$		--	5	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 30V,$ $I_D = 20A,$ $R_G = 3\Omega$	--	10.5	--	ns
Turn-on Rise Time	$t_r$		--	4.5	--	
Turn-off Delay Time	$t_{d(off)}$		--	29.5	--	
Turn-off Fall Time	$t_f$		--	8	--	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Body Diode Current	$I_S$	$T_C = 25^\circ\text{C}$	--	--	45	A
Body Diode Voltage	$V_{SD}$	$T_J = 25^\circ\text{C}, I_{SD} = 14A, V_{GS} = 0V$	--	--	1.2	V
Reverse Recovery Charge	$Q_{rr}$	$I_F = 20A, V_{GS} = 0V$ $di/dt = 500A/\mu s$	--	58	--	nC
Reverse Recovery Time	$T_{rr}$		--	17	--	ns

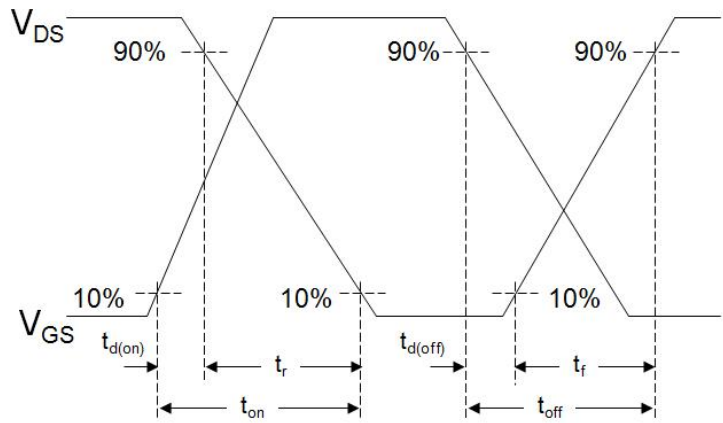
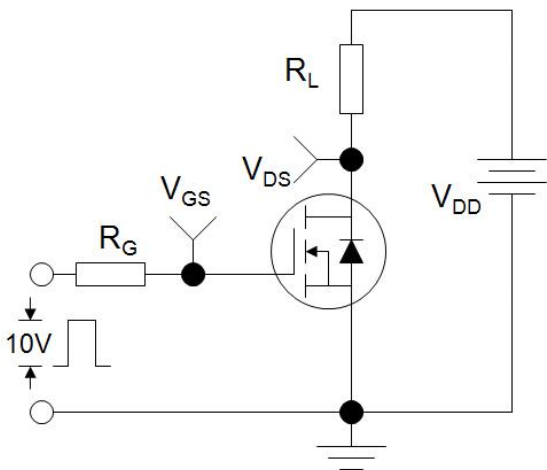
### Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. EAS condition :  $T_J = 25^\circ\text{C}, V_{DD} = 50V, V_{GS} = 10V, L = 0.5mH, R_G = 25\Omega$
3. Identical low side and high side switch with identical  $R_G$

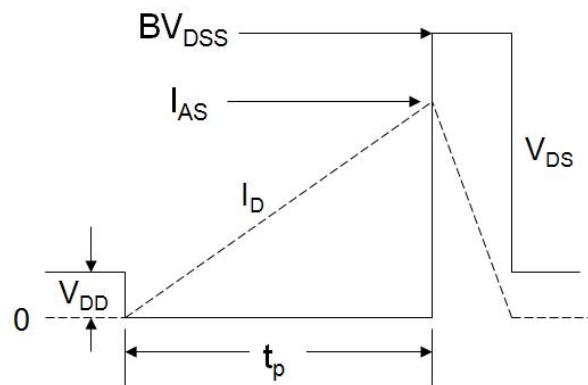
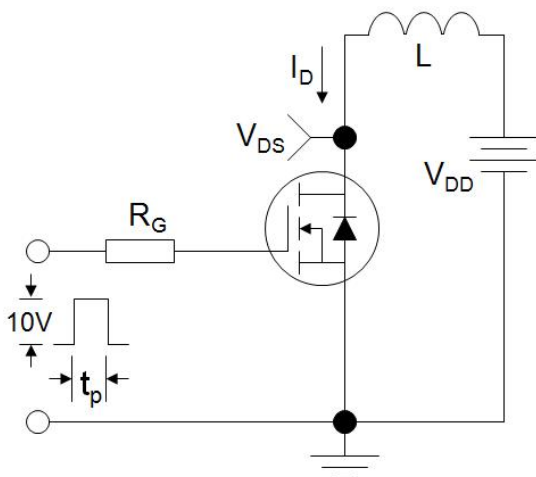
### Gate Charge Test Circuit



### Switch Time Test Circuit

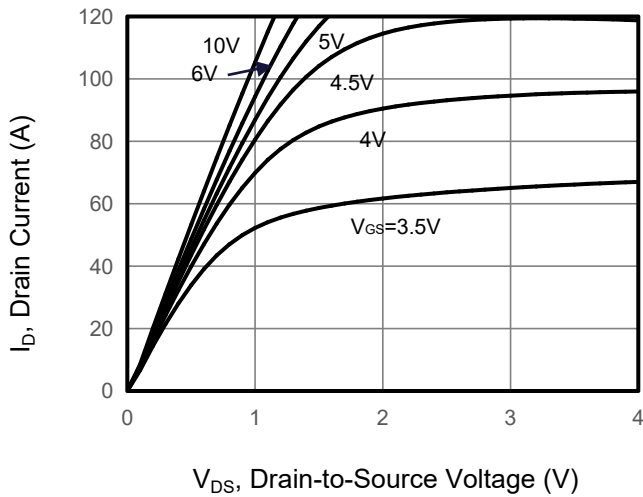


### EAS Test Circuit

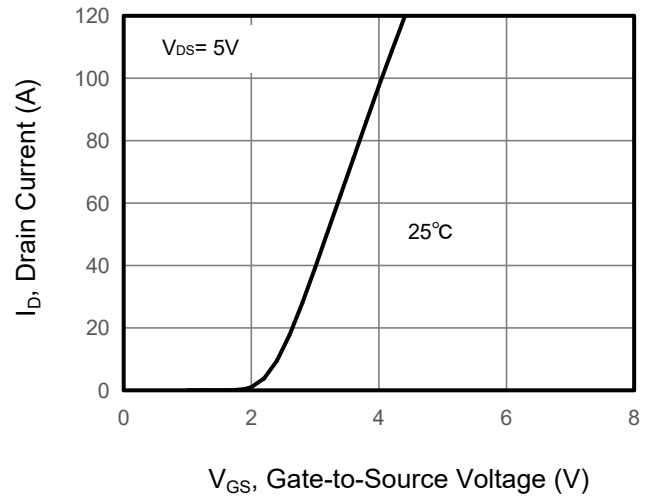


Typical Characteristics  $T_J = 25^\circ\text{C}$ , unless otherwise noted

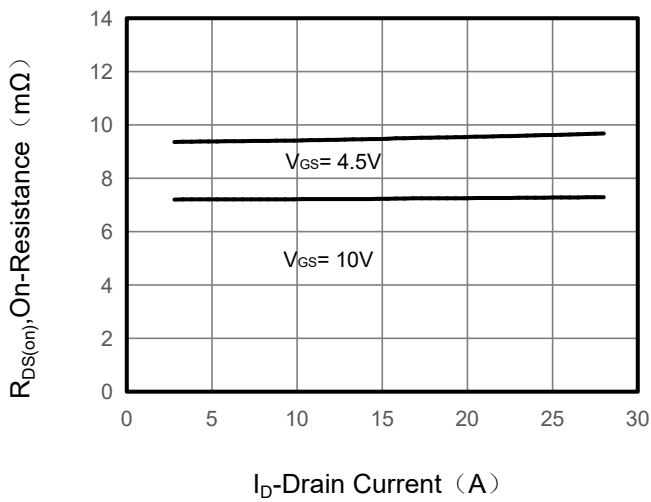
**Figure 1. Output Characteristics**



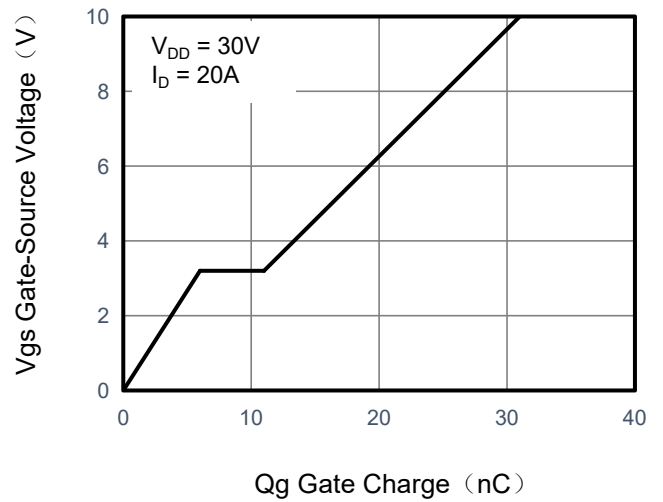
**Figure 2. Transfer Characteristics**



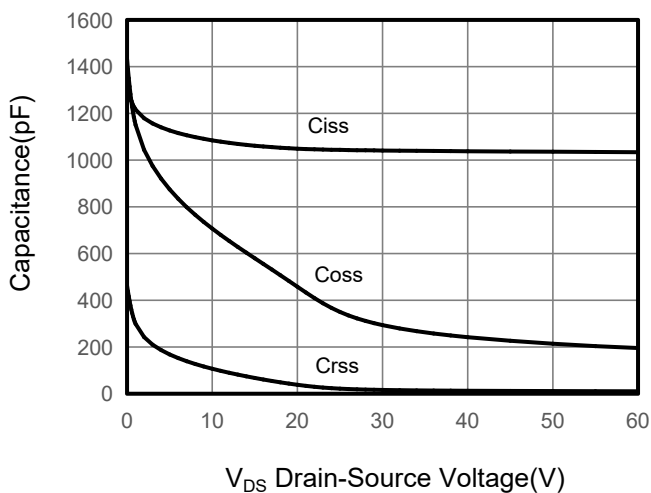
**Figure 3. Drain Source On Resistance**



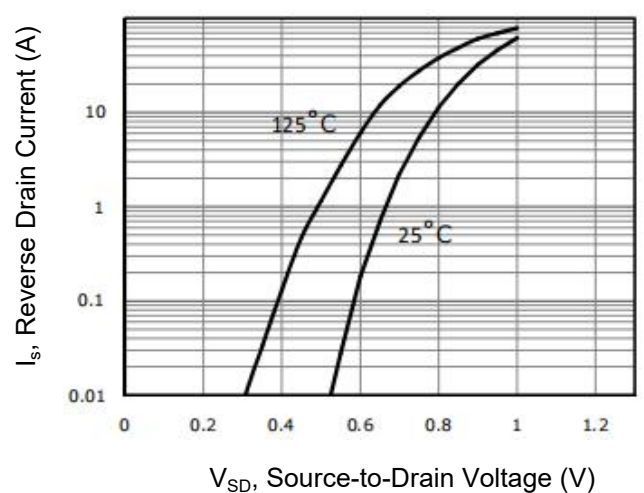
**Figure 4. Gate Charge**



**Figure 5. Capacitance**



**Figure 6. Source-Drain Diode Forward**



Typical Characteristics  $T_J = 25^\circ\text{C}$ , unless otherwise noted

Figure 7. Drain-Source On-Resistance

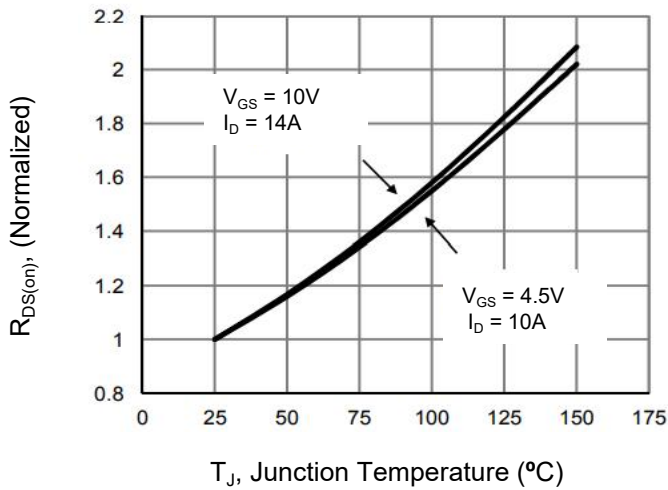


Figure 8. Safe Operation Area

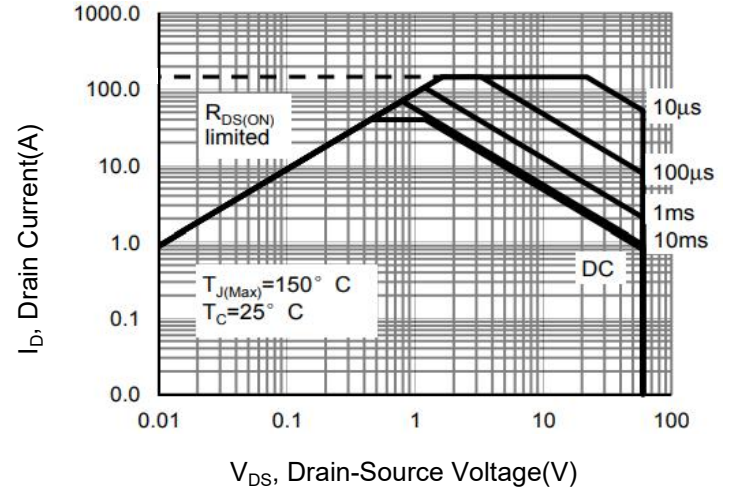
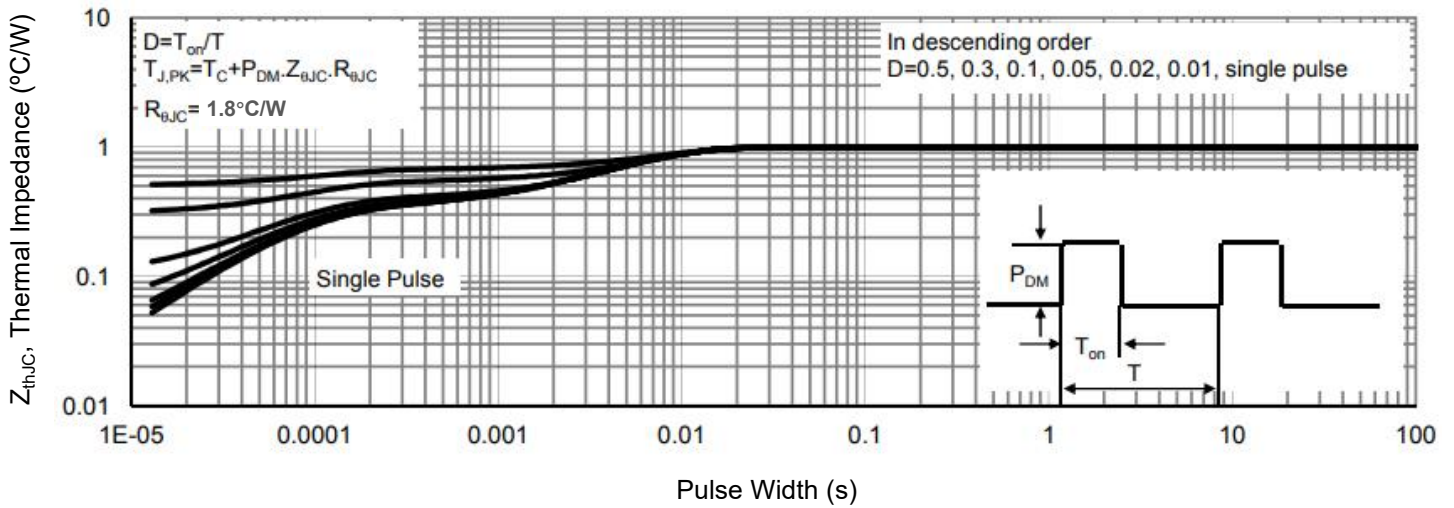
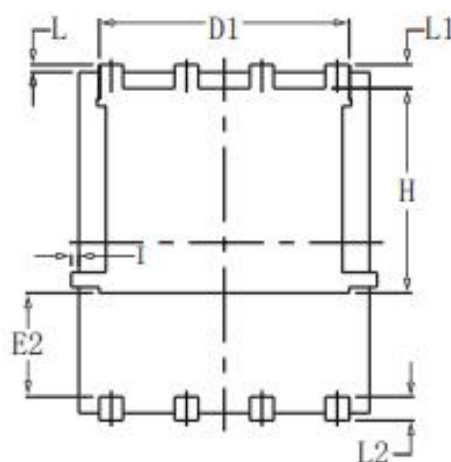
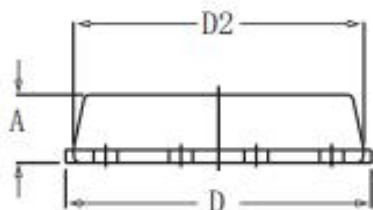
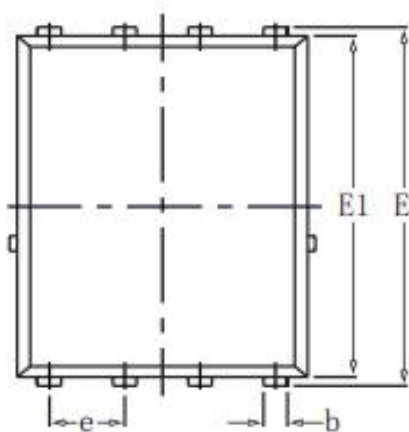


Figure 9. Normalized Maximum Transient Thermal Impedance



## DFN5X6-8L Package information



SYMBOL	COMMON			
	MM		INCH	
	MIN	MAX	MIN	MAX
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.970	0.0324	0.0382
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.59	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	-	0.0630	-
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	-	0.18	-	0.0070

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